



PRODUCT DATA SHEET



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Datasheet



Resources



Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

Features

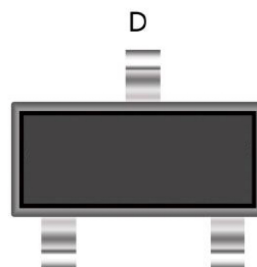
- Lead Free Product is Acquired
- Surface Mount Package
- P-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

Application

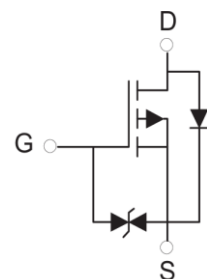
- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics

Product Summary

V_{DS}	$R_{DS(on)}$ TYP	I_D
-20V	430mΩ@-4.5V	-0.66A
	624mΩ@-2.5V	



SOT-23 top view



Schematic diagram

Absolute Maximum Ratings (TA=25°Cunless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		-20	V
V _{GS}	Gate-Source Voltage		±10	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-0.66	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	-1.2	A
I _b	Continuous Drain Current	Tc=25°C	-0.66	A
P _D	Maximum Power Dissipation	Tc=25°C	0.35	W
R _{θJA}	Thermal Resistance Junction-to-Ambient		357	°C/W

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	--	--	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	--	--	±20	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.35	-0.45	-1.10	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-1.0A	--	430	520	mΩ
		V _{GS} =-2.5V, I _D =-0.8A	--	624	700	mΩ
		V _{GS} =-1.8V, I _D =-0.5A	--	950	--	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	115	--	pF
C _{OSS}	Output Capacitance		--	15	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	8.8	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =-10V, I _D =-0.5A, V _{GS} =-4.5V	--	1.25	--	nC
Q _{gs}	Gate Source Charge		--	0.35	--	nC
Q _{gd}	Gate Drain Charge		--	0.29	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-10V, I _D =-0.2A, V _{GS} =-4.5V, R _G =10Ω	--	9	--	nS
t _r	Turn-on Rise Time		--	5.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	30.8	--	nS
t _f	Turn-Off Fall Time		--	20	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25℃, Is=-0.66A	--	--	-1.2	V

Typical Operating Characteristics

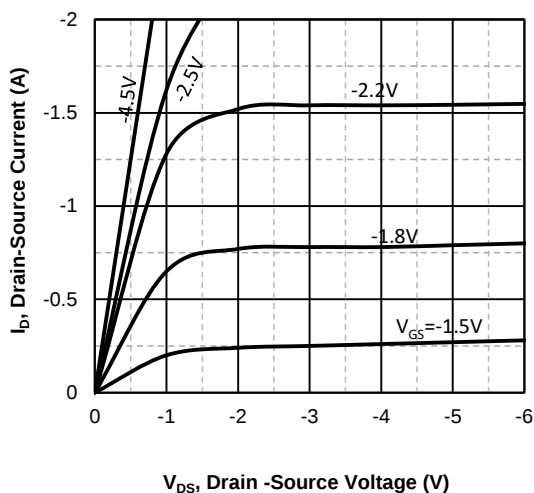


Fig1. Typical Output Characteristics

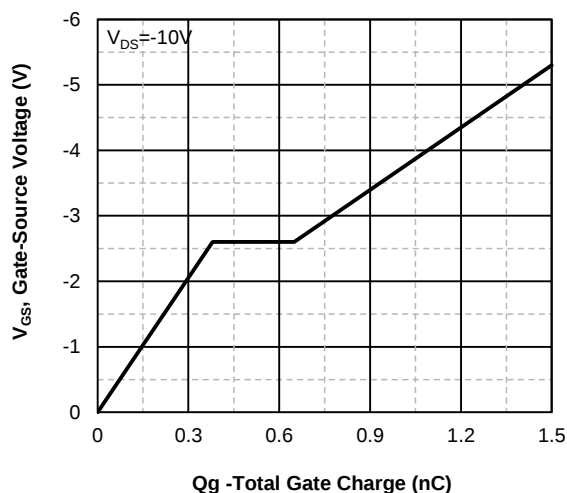


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

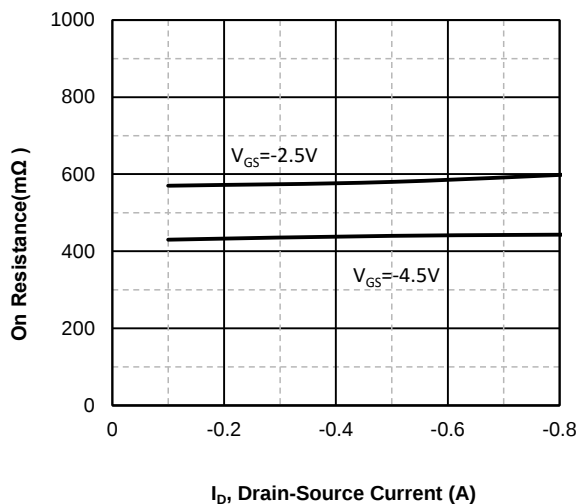


Fig3. Drain-Source on Resistance

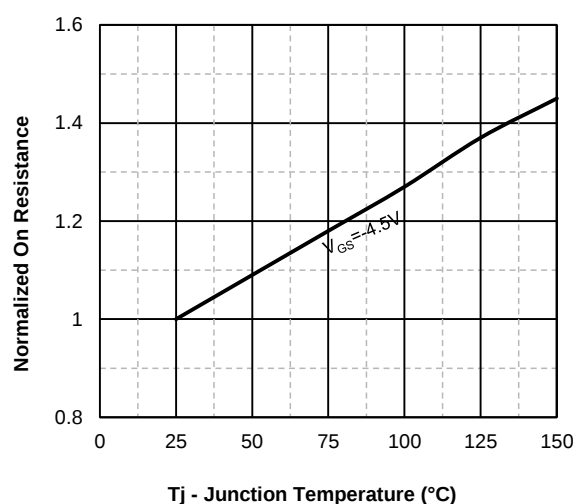


Fig4. Normalized On-Resistance Vs. Temperature

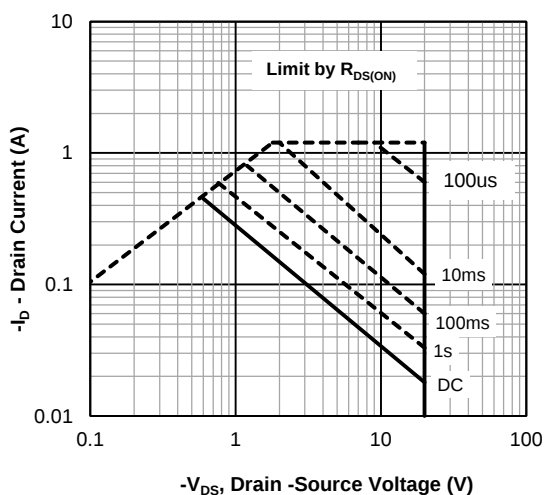


Fig5. Maximum Safe Operating Area

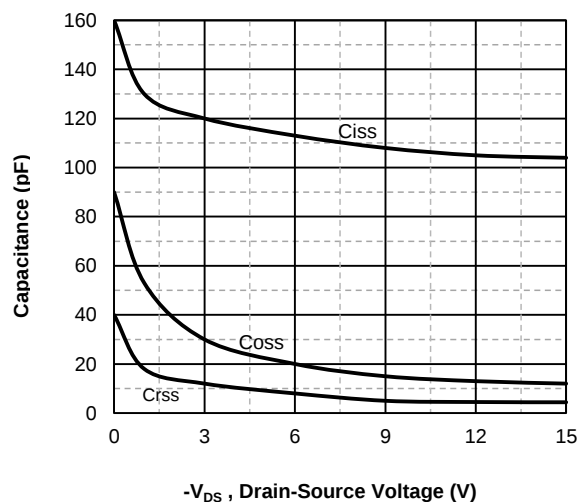
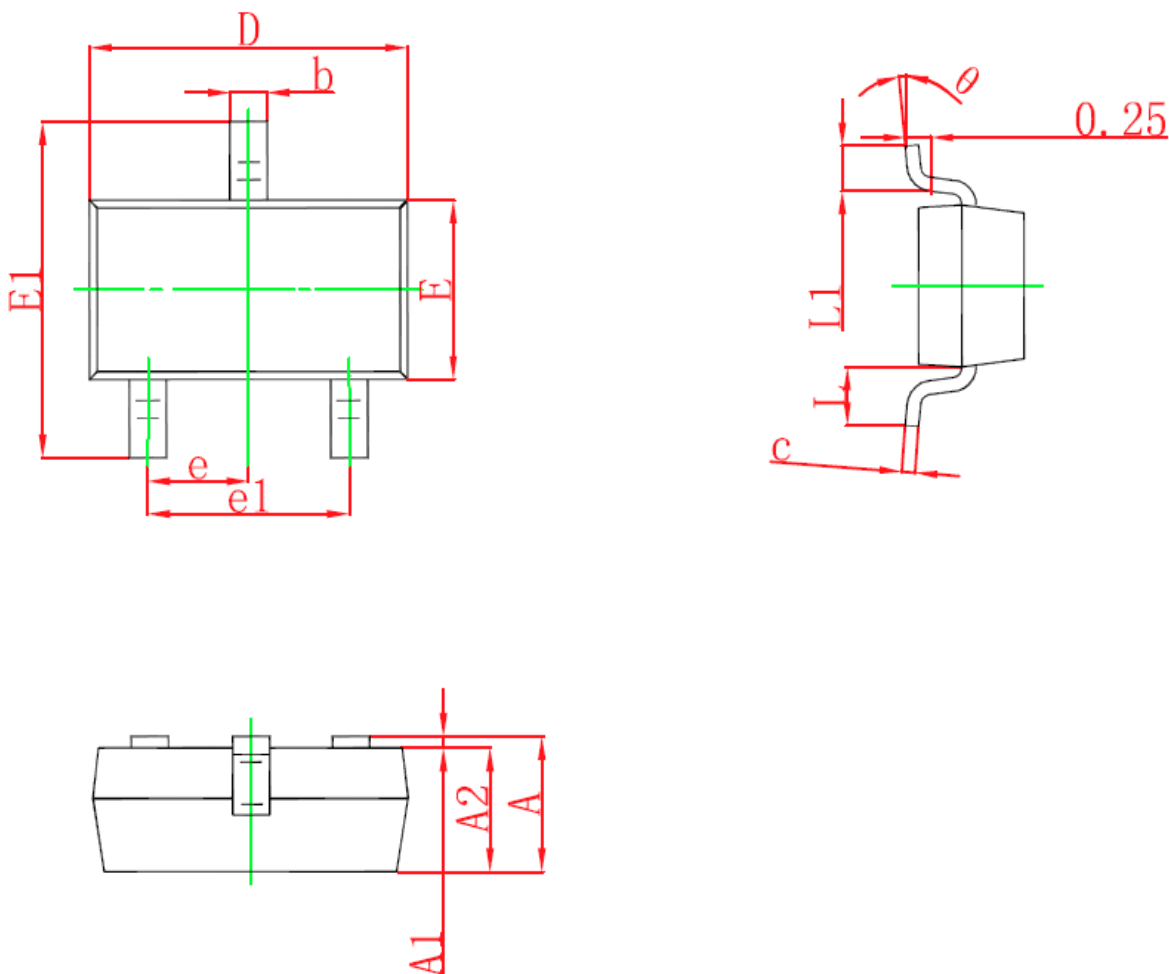


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

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